
	<p><b>SI7888DP-T1-E3</b></p>
	<p><b>Hersteller-Teilenummer:</b> <a href="#">SI7888DP-T1-E3</a></p> <p><b>Hersteller / Marke:</b> <a href="#">Vishay / Siliconix</a></p> <p><b>Teil der Beschreibung:</b> MOSFET N-CH 30V 9.4A PPAK SO-8</p> <p><b>Datenblätter:</b>  <a href="#">SI7888DP-T1-E3.pdf</a></p> <p><b>RoHs Status:</b> Bleifrei / RoHS-konform</p> <p><b>Lagerzustand:</b> New original, 12488 pcs Stock Available.</p> <p><b>Liefern von:</b> Hong Kong</p> <p><b>Versandweg:</b> DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

### Spezifikationen

Teilenummer	<a href="#">SI7888DP-T1-E3</a>
Hersteller	<a href="#">Vishay / Siliconix</a>
Beschreibung	MOSFET N-CH 30V 9.4A PPAK SO-8
Kategorie	<a href="#">Diskrete Halbleiterprodukte &gt; Transistoren-FETs,</a>
Teilstatus	12488 pcs Stock
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	PowerPAK® SO-8
Supplier Device-Gehäuse	PowerPAK® SO-8
Verlustleistung (max)	1.8W (Ta)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	30V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	9.4A (Ta)
Rds On (Max) @ Id, Vgs	12 mOhm @ 12.4A, 10V
VGS (th) (Max) @ Id	2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	10.5nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	-
Verpackung	Tape & Reel (TR)














































SI7888DP-T1-E3 ist neu im Original, Suche SI7888DP-T1-E3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI7888DP-T1-E3 Vishay / Siliconix mit Garantie und Vertrauen. Anfrage SI7888DP-T1-E3: [Info@Y-IC.com](mailto:Info@Y-IC.com)

Sie können auch interessiert sein:

 <p><b>SI7892ADP-T1-GE3.</b> VIS SI7892ADP-T1-GE3. VIS</p>	 <p><b>SI7888DP</b> SILICONIX SI7888DP SILICONIX</p>	 <p><b>SI7892ADP-T1-E3</b> VISHAY SI7892ADP-T1-E3 VISHAY</p>	 <p><b>SI7888DP-T1</b> VISHAY VISHAY QFN</p>
 <p><b>SI7888DP-T1-GE3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 9.4A PPAK SO-8</p>	 <p><b>SI7888DP-T1-GE3</b> Vishay / Siliconix MOSFET N-CH 30V 9.4A PPAK SO-8</p>	 <p><b>SI7892ADP-T1-GE3</b> V SI7892ADP-T1-GE3 V</p>	 <p><b>SI7888DP-T1-E3</b> Electro-Films (EFI) / Vishay MOSFET N-CH 30V 9.4A PPAK SO-8</p>

### heiße Teile

Mehr

 SI7880ADP-T1-E3	 SI7880ADP-T1-E3	 SI7880ADP-T1-GE3	 SI7880ADP-T1-GE3	 SI7880DP-T1-GE3
 SI7882DP-T1-E3	 SI7882DP-T1-E3	 SI7882DP-T1-GE3	 SI7882DP-T1-GE3	 SI7884BDP
 SI7884BDP-T1-E3	 SI7884BDP-T1-E3	 SI7884BDP-T1-GE3	 SI7884BDP-T1-GE3	 SI7884DP-T1-E3
 SI7884DP-T1-GE3	 SI7886ADP-T1-E3	 SI7886ADP-T1-E3	 SI7886ADP-T1-GE3	 SI7886ADP-T1-GE3
 SI7886DP	 SI7886DP-T1	 SI7886DP-T1-E3	 SI7886DP-T1-GE3	 SI7888DP-T1-E3
 SI7888DP-T1-GE3	 SI7888DP-T1-GE3	 SI7892ADP-T1-E3	 SI7892ADP-T1-GE3	 SI7892ADP-T1-GE3.
 SI7892BDP-T1-E3	 SI7892BDP-T1-E3	 SI7892BDP-T1-GE3	 SI7892BDP-T1-GE3	 SI7892DP
 SI7892DP-T1	 SI7892DP-T1-E3	 SI7892DP-T1-GE3	 SI7898DP	 SI7898DP-T1-E3
 SI7898DP-T1-E3	 SI7898DP-T1-GE3	 SI7898DP-T1-GE3	 SI7900ADN	 SI7900AEDN
 SI7900AEDN-T1	 SI7900AEDN-T1-E3	 SI7900AEDN-T1-E3	 SI7900AEDN-T1-GE3	 SI7900AEDN-T1-GE3

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